

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V$ $R_L=33$	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V

I_L $I_G=1.2I_{GT}$

ORDERING INFORMATION

<u>J</u>	<u>ST</u>	<u>08</u>	<u>A</u>	<u>-1200</u>	<u>BW</u>
JieJie Microelectronics Co., Ltd.	Triacs	$I_{T(RMS)}:8A$			
		<u>A:TO-220A(Ins)</u>			<u>BW:IGT1-3 50mA</u>
				<u>1200:V_{DRM} /V_{RRM} 1200V</u>	

MARKING

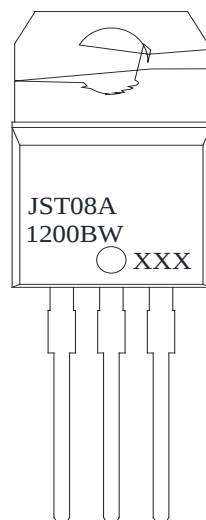


FIG.1: Maximum power dissipation versus RMS
on-state

ORDERING INFORMATION

Order code	Voltage V _{DRM} /V _{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery	RMRRM

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